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	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	493	(marking near3 defect\$3)and (wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 16:36
2	BRS	L2	108	(marking near3 defect\$3)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 16:55
3	BRS	L3	20	2 and photomask	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 18:05
4	BRS	L4	14	3 and @ad<20011116	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 17:02
5	BRS	L5	0	4 and dense near3 patterns	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 16:55

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L6	0	4 and dense and patterns	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 16:44
7	BRS	L7	0	4 and dense near3 region	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 16:44
8	BRS	L8	0	4 and repair and clean\$3	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 18:0611/08
9	BRS	L9	0	4 and repair\$3	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 16:4611/08
10	BRS	L10	0	4 and pellicle	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 16:5611/08

	Type	L #	Hits	Search Text	DBs	Time Stamp
11	BRS	L11	14	2 and 4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 16:50
12	BRS	L12	2444	(marking near3 defect\$3 or mark\$2)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 16:58
13	BRS	L13	1770	12 and @ad<20011116	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 16:58
14	BRS	L14	16	13 and dense near3 patterns	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 16:56
15	BRS	L16	0	15 and pellicle	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 16:56

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L15	5	14 and repair and clean\$3	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 16:58
17	BRS	L17	329	(marking or mark\$2)near3 defect\$3 and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 16:58
18	BRS	L18	249	17 and @ad<20011116	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 18:0511/08 8
19	BRS	L19	13	18 and repair and clean\$3	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 16:5811/08 3
20	BRS	L20	0	4 and (repetot\$3 or repepeat\$3)near3 pattern\$1	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 17:0511/08 3

	Type	L #	Hits	Search Text	DBs	Time Stamp
21	BRS	L21	11	4 and (repetit\$3 or repepeat\$3)near3 pattern\$1	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 17:05
22	BRS	L22	0	21 and(non-repetit\$3 or nonrepetit\$3)near3 pattern\$1	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 17:06
23	BRS	L23	0	21 and (contrast near3 data or grey near3 scale)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 17:08
24	BRS	L24	11	21 and threshold	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 17:08
25	BRS	L25	11	24 and (cell or array matrix)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 18:04

	Type	L #	Hits	Search Text	DBs	Time Stamp
26	BRS	L26	0	4 and photolithograph	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 18:04
27	BRS	L27	0	1 and photolithograph	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 18:04
28	BRS	L28	15	1 and lithography	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 18:0511/08
29	BRS	L29	0	4 and lithography	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 18:0511/08
30	BRS	L30	0	28 and photomask	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 18:05

	Type	L #	Hits	Search Text	DBs	Time Stamp
31	BRS	L31	7	28 and @ad<20011116	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 18:05
32	BRS	L32	0	31 and repair and clean\$3	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/11/08 18:06

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L Number	Hits	Search Text	DB	Time stamp
1	493	(marking near3 defect\$3)and (wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:36
2	108	(marking near3 defect\$3)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:55
3	20	((marking near3 defect\$3)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3) and photomask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 18:05
4	14	((((marking near3 defect\$3)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3) and photomask) and @ad<20011116	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 17:02
5	0	((((marking near3 defect\$3)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3) and photomask) and @ad<20011116) and dense near3 patterns	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:55
6	0	((((marking near3 defect\$3)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3) and photomask) and @ad<20011116) and dense and patterns	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:44
7	0	((((marking near3 defect\$3)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3) and photomask) and @ad<20011116) and dense near3 region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:44
8	0	((((marking near3 defect\$3)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3) and photomask) and @ad<20011116) and repair and clean\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 18:06
9	0	((((marking near3 defect\$3)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3) and photomask) and @ad<20011116) and repair\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:46
10	0	((((marking near3 defect\$3)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3) and photomask) and @ad<20011116) and pellicle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:56
11	14	((marking near3 defect\$3)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3) and (((marking near3 defect\$3)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3) and photomask) and @ad<20011116)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:50
12	2444	(marking near3 defect\$3 or mark\$2)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:58
13	1770	((marking near3 defect\$3 or mark\$2)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3) and @ad<20011116	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:58

14	16	((marking near3 defect\$3 or mark\$2)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3) and @ad<20011116) and dense near3 patterns	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:56
16	0	(((((marking near3 defect\$3 or mark\$2)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3) and @ad<20011116) and dense near3 patterns) and repair and clean\$3) and pellicle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:56
15	5	((marking near3 defect\$3 or mark\$2)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3) and @ad<20011116) and dense near3 patterns) and repair and clean\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:58
17	329	(marking or mark\$2)near3 defect\$3 and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:58
18	249	((marking or mark\$2)near3 defect\$3 and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3) and @ad<20011116	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 18:05
19	13	((marking or mark\$2)near3 defect\$3 and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3) and @ad<20011116) and repair and clean\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 16:58
20	0	(((((marking near3 defect\$3)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3) and photomask) and @ad<20011116) and (repetot\$3 or repepeat\$3)near3 pattern\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 17:05
21	11	(((((marking near3 defect\$3)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3) and photomask) and @ad<20011116) and (repetit\$3 or repepeat\$3)near3 pattern\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 17:05
22	0	(((((marking near3 defect\$3)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3) and photomask) and @ad<20011116) and (repetit\$3 or repepeat\$3)near3 pattern\$1) and(non-repetit\$3 or nonrepetit\$3)near3 pattern\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 17:06
23	0	(((((marking near3 defect\$3)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3) and photomask) and @ad<20011116) and (repetit\$3 or repepeat\$3)near3 pattern\$1) and (contrast near3 data or grey near3 scale)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 17:08
24	11	(((((marking near3 defect\$3)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3) and photomask) and @ad<20011116) and (repetit\$3 or repepeat\$3)near3 pattern\$1) and threshold	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 17:08
25	11	(((((marking near3 defect\$3)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3) and photomask) and @ad<20011116) and (repetit\$3 or repepeat\$3)near3 pattern\$1) and threshold) and (cell or array matrix)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 18:04
26	0	(((((marking near3 defect\$3)and(wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3) and photomask) and @ad<20011116) and photolithograph	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 18:04

27	0	((marking near3 defect\$3)and (wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)) and photolithograph	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 18:04
28	15	((marking near3 defect\$3)and (wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)) and lithography	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 18:05
29	0	((((marking near3 defect\$3)and (wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)near3 inspect\$3) and photomask) and @ad<20011116) and lithography	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 18:05
30	0	((marking near3 defect\$3)and (wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)) and lithography) and photomask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 18:05
31	7	((marking near3 defect\$3)and (wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)) and lithography) and @ad<20011116	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 18:05
32	0	((((marking near3 defect\$3)and (wafer\$1 or semiconductor\$1 or IC or intergrated adj circuit)) and lithography) and @ad<20011116) and repair and clean\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/11/08 18:06